

I. Power section

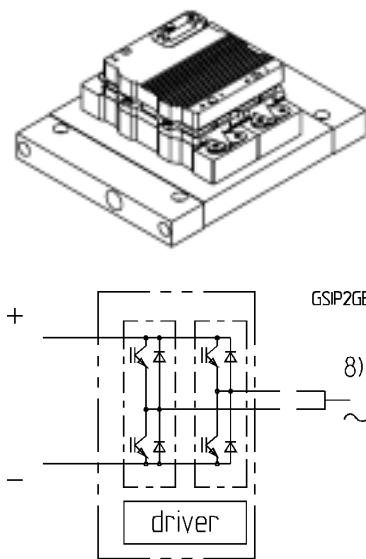
Absolute maximum ratings		$T_s = 25^\circ\text{C}$ unless otherwise specified		
Symbol	Conditions	Values	Units	
IGBT				
$V_{CES}^{(1)}$	Operating DC link voltage	1700 1200 ± 20	V V V	
V_{GES}		1200 (900)	A	
I_c	$T_s = 25$ (70) °C			
Inverse diode				
$I_F = -I_c$	$T_s = 25$ (70) °C	900 (670)	A	
I_{FSM}	$T_j = 150$ °C, $t_p = 10\text{ms}$; sin	8640	A	
I^2t (Diode)	Diode, $T_i = 150$ °C, 10ms	373	kA²s	
T_j , (T_{stg})		-40...+150 (125)	°C	
V_{isol}	rms, AC, 1min per AC terminal, rms, $T_s = 70$ °C, $T_{terminal} < 115$ °C	4000 400	V A	
$I_{AC\text{-terminal}}$				

Characteristics $T_s = 25^\circ\text{C}$ unless otherwise specified				
Symbol	Conditions	min.	typ.	max.
IGBT				
V_{CEsat}	$I_c = 600\text{A}$, $T_j = 25$ (125) °C; measured at terminal	–	1,9 (2,2)	2,4
V_{CEO}	$T_j = 25$ (125) °C; at terminal	–	1,0 (0,9)	1,2 (1,1)
r_{CE}	$T_j = 25$ (125) °C; at terminal	–	1,5 (2,1)	1,9 (2,5)
I_{CES}	$V_{GE}=0$, $V_{CE}=V_{CES}$, $T_j=25$ (125) °C	–	2,4 (144)	–
$E_{on} + E_{off}$	$I_c=600\text{A}$, $V_{cc}=900\text{V}$ $T_j=125$ °C	–	484	–
	$V_{cc}=1200\text{V}$	–	714	–
L_{CE}	top, bottom	–	6	–
C_{CHC}	per phase, AC side	–	2,0	–
$R_{CC\text{-EE}}$	terminal-chip, $T_j=25$ °C	–	0,25	–
Inverse diode				
$V_F = V_{EC}$	$I_F = 600\text{A}$; $T_j = 25$ (125) °C measured at terminal	–	1,6 (1,5)	2,0
V_{TO}	$T_j = 25$ (125) °C	–	1,1 (0,8)	1,3 (1,0)
r_T	$T_j = 25$ (125) °C	–	0,8 (1,2)	1,2 (1,5)
E_{RR}	$I_c=600\text{A}$, $V_{cc}=900\text{V}$ $T_j=125$ °C	–	86	–
	$V_{cc}=1200\text{V}$	–	102	–
Mechanical data				
M_{dc}	DC terminals, SI Units	6	–	8
M_{ac}	AC terminals, SI Units	13	–	15
w	SKiiP® 3 System w/o heat sink	–	1,7	–
w	heat sink	–	4,3	–
Thermal characteristics (NWK 40; 8l/min; 50%glyc.); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc. IEC 60747-15)				
$R_{thjsIGBT}$	per IGBT	–	–	0,026 °C/W
$R_{thjsdiode}$	per diode	–	–	0,050 °C/W
Z_{th}	R_i (mK/W) (max. values)		tau(s)	
	1 2 3 4	1	2	3 4
$IGBT_{jr}$	2,8 11,6 13,6 0,0	69,00	0,35	0,02 1,0
diode _{jr}	4,0 6,0 26,0 26,0	50,0	5,0	0,25 0,04
heatsink _{ra}	5,5 4,8 1,1 0,6	48	15	2,8 0,4

SKiiP® 3**SK integrated intelligent Power 2-pack****SKiiP 1203GB173-2DW**

Preliminary data

Case S23



Features

- SKiiP technology inside
- Trench IGBTs
- CAL HD diode technology
- integrated current sensor
- integrated temperature sensor
- integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 3 System)
- IEC 68T.1 (climate) 40/125/56 (SKiiP® 3 power section)
- UL recognized File no. E63532 (SKiiP® 3 power section)

- 1) with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)
- 8) AC connection busbars must be connected by the user; copper busbars available on request

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SKiiP 1203GB173-2DW

SKiiP 3®

SK integrated intelligent Power

SKiiP 1203GB173-2DW

Preliminary data

Gate driver features

- CMOS compatible inputs
- wide range power supply
- integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- short circuit protection
- over current protection
- over voltage protection (option)
- power supply protected against under voltage
- interlock of top/bottom switch
- isolation by transformers
- fibre optic interface (option for GB-types only)
- IEC 68T.1 (climate) 40/85/56 (SKiiP® 3 gate driver)

II. Integrated gate driver

Absolute maximum ratings

Symbol	Term	Value	Unit
V_{S2}	unstabilized 24V power supply	30	V
V_{iH}	input signal voltage (high)	15 + 0,3	V
dv/dt	secondary to primary side	75	kV/μs
V_{isoIO}	input / output (AC, rms, 2 s)	4000	V
V_{isoPD}	partial discharge extinction voltage, rms, $Q_{PD} \leq 10 \text{ pC}$	1500	V
V_{isol12}	output 1 / output 2 (AC, rms, 2s)	1500	V
f	switching frequency	13	kHz
T_{op} (T_{stg})	operating / storage temperature	- 40 ... + 85	°C

Electrical characteristics ($T_a = 25^\circ\text{C}$)

Symbol	Term	min	typ	max.	Units
V_{S2}	supply voltage non stabilized	13	24	27	V
I_{S2}	$V_{S2} = 24\text{V}$	$274 + 23*f / \text{kHz} + 0,00022 * (I_{AC}/A)^2$			mA
V_{IT+}	input threshold voltage (High)	11,2	—	—	V
V_{IT-}	input threshold voltage (Low)	—	—	5,4	V
R_{in}	input resistance	—	10	—	kΩ
C_{in}	input capacitance	—	1	—	nF
$t_{d(on)IO}$	input-output turn-on propagation time	—	1,1	—	μs
$t_{d(off)IO}$	input-output turn-off propagation time	—	1,1	—	μs
$t_pERRRESET$	error memory reset time	—	9	—	μs
t_{TD}	top/bottom switch: interlock time	—	3,3	—	μs
$I_{analog OUT}$	max. 5mA ; 8 V corresponds to 15 V supply voltage for external components; max load current	—	1000	—	A
I_{S1out}		—	—	50	mA
I_{TRIPSC}	over current trip level ($I_{analog OUT} = 10\text{V}$)	—	1250	—	A
T_{tp}	over temperature protection	110	—	120	°C
U_{DCTRIP}	U_{DC} -protection ($U_{analog OUT} = 9\text{V}$) (option for GB types)	not implemented	—	—	V

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